



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

2SA935 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.75 W ($T_{amb}=25^{\circ}C$)

Collector current

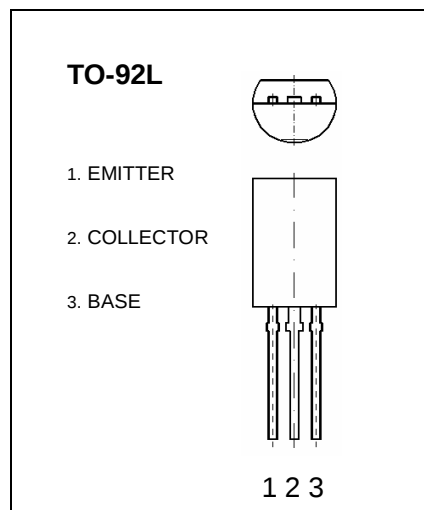
I_{CM} : -0.7 A

Collector-base voltage

$V_{(BR)CBO}$: -80 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-2mA, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-3V, I_C=-100mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.4	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking			